

# BZX84B4V7LT1, BZX84C2V4LT1 Series

## Zener Voltage Regulators

### 225 mW SOT-23 Surface Mount

This series of Zener diodes is offered in the convenient, surface mount plastic SOT-23 package. These devices are designed to provide voltage regulation with minimum space requirement. They are well suited for applications such as cellular phones, hand held portables, and high density PC boards.

#### Features

- 225 mW Rating on FR-4 or FR-5 Board
- Zener Breakdown Voltage Range – 2.4 V to 75 V
- Package Designed for Optimal Automated Board Assembly
- Small Package Size for High Density Applications
- ESD Rating of Class 3 (>16 KV) per Human Body Model
- Tight Tolerance Series Available (See Page 4)
- Pb-Free Packages are Available

#### Mechanical Characteristics

**CASE:** Void-free, transfer-molded, thermosetting plastic case

**FINISH:** Corrosion resistant finish, easily Solderable

**MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:**  
260°C for 10 Seconds

**POLARITY:** Cathode indicated by polarity band

**FLAMMABILITY RATING:** UL 94 V-0

#### MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Total Power Dissipation on FR-5 Board, (Note 1) @ $T_A = 25^\circ\text{C}$ Derated above $25^\circ\text{C}$	$P_D$	225	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	1.8	$\text{mW}/^\circ\text{C}$
Total Power Dissipation on Alumina Substrate, (Note 2) @ $T_A = 25^\circ\text{C}$ Derated above $25^\circ\text{C}$	$P_D$	300	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	2.4	$\text{mW}/^\circ\text{C}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

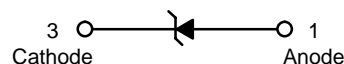
1. FR-5 = 1.0 X 0.75 X 0.62 in.

2. Alumina = 0.4 X 0.3 X 0.024 in., 99.5% alumina.

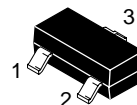


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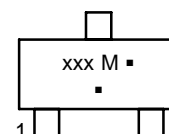
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#### MARKING DIAGRAM



SOT-23  
CASE 318  
STYLE 8



xxx = Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping†
BZX84CxxxLT1	SOT-23	3000/Tape & Reel
BZX84CxxxLT1G	SOT-23 (Pb-Free)	3000/Tape & Reel
BZX84CxxxLT3	SOT-23	10,000/Tape & Reel
BZX84CxxxLT3G	SOT-23 (Pb-Free)	10,000/Tape & Reel
BZX84BxxxLT1	SOT-23	3000/Tape & Reel
BZX84BxxxLT1G	SOT-23 (Pb-Free)	3000/Tape & Reel
BZX84BxxxLT3	SOT-23	10,000/Tape & Reel
BZX84BxxxLT3G	SOT-23 (Pb-Free)	10,000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

#### DEVICE MARKING INFORMATION

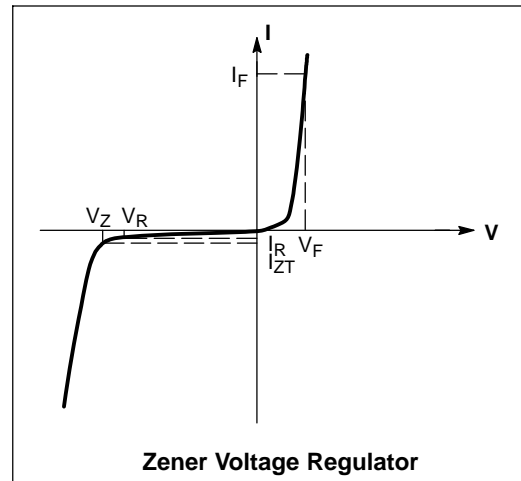
See specific marking information in the device marking column of the Electrical Characteristics table on page 3 of this data sheet.

## BZX84B4V7LT1, BZX84C2V4LT1 Series

### ELECTRICAL CHARACTERISTICS

(Pinout: 1-Anode, 2-No Connection, 3-Cathode) ( $T_A = 25^\circ\text{C}$  unless otherwise noted,  $V_F = 0.95\text{ V Max. @ } I_F = 10\text{ mA}$ )

Symbol	Parameter
$V_Z$	Reverse Zener Voltage @ $I_{ZT}$
$I_{ZT}$	Reverse Current
$Z_{ZT}$	Maximum Zener Impedance @ $I_{ZT}$
$I_R$	Reverse Leakage Current @ $V_R$
$V_R$	Reverse Voltage
$I_F$	Forward Current
$V_F$	Forward Voltage @ $I_F$
$\Theta_{VZ}$	Maximum Temperature Coefficient of $V_Z$
C	Max. Capacitance @ $V_R = 0$ and $f = 1\text{ MHz}$



## BZX84B4V7LT1, BZX84C2V4LT1 Series

### ELECTRICAL CHARACTERISTICS – BZX84CxxxLT1 SERIES (STANDARD TOLERANCE)

(Pinout: 1-Anode, 2-No Connection, 3-Cathode) ( $T_A = 25^\circ\text{C}$  unless otherwise noted,  $V_F = 0.90\text{ V Max.}$  @  $I_F = 10\text{ mA}$ )  
 (Devices listed in **bold, italic** are ON Semiconductor Preferred devices.)

Device*	Device Marking	V <sub>Z1</sub> (Volts) @ I <sub>ZT1</sub> = 5 mA (Note 3)			Z <sub>ZT1</sub> (Ω) @ I <sub>ZT1</sub> = 5 mA	V <sub>Z2</sub> (V) @ I <sub>ZT2</sub> = 1 mA (Note 3)		Z <sub>ZT2</sub> (Ω) @ I <sub>ZT2</sub> = 1 mA	V <sub>Z3</sub> (V) @ I <sub>ZT3</sub> = 20 mA (Note 3)		Z <sub>ZT3</sub> (Ω) @ I <sub>ZT3</sub> = 20 mA	Max Reverse Leakage Current		θ <sub>VZ</sub> (mV/k) @ I <sub>ZT1</sub> = 5 mA		C (pF) @ V <sub>R</sub> = 0 f = 1 MHz
		Min	Nom	Max		Min	Max		Min	Max		I <sub>R</sub> (μA)	V <sub>R</sub> (Volts)	Min	Max	
BZX84C2V4LT1, G	Z11	2.2	2.4	2.6	100	1.7	2.1	600	2.6	3.2	50	50	1	-3.5	0	450
BZX84C2V7LT1, G	Z12	2.5	2.7	2.9	100	1.9	2.4	600	3	3.6	50	20	1	-3.5	0	450
BZX84C3V0LT1, G	Z13	2.8	3	3.2	95	2.1	2.7	600	3.3	3.9	50	10	1	-3.5	0	450
BZX84C3V3LT1, G	Z14	3.1	3.3	3.5	95	2.3	2.9	600	3.6	4.2	40	5	1	-3.5	0	450
BZX84C3V6LT1, G	Z15	3.4	3.6	3.8	90	2.7	3.3	600	3.9	4.5	40	5	1	-3.5	0	450
BZX84C3V9LT1, G	Z16	3.7	3.9	4.1	90	2.9	3.5	600	4.1	4.7	30	3	1	-3.5	-2.5	450
BZX84C4V3LT1, G	W9	4	4.3	4.6	90	3.3	4	600	4.4	5.1	30	3	1	-3.5	0	450
<b>BZX84C4V7LT1, G</b>	<b>Z1</b>	<b>4.4</b>	<b>4.7</b>	<b>5</b>	<b>80</b>	<b>3.7</b>	<b>4.7</b>	<b>500</b>	<b>4.5</b>	<b>5.4</b>	<b>15</b>	<b>3</b>	<b>2</b>	<b>-3.5</b>	<b>0.2</b>	<b>260</b>
<b>BZX84C5V1LT1, G</b>	<b>Z2</b>	<b>4.8</b>	<b>5.1</b>	<b>5.4</b>	<b>60</b>	<b>4.2</b>	<b>5.3</b>	<b>480</b>	<b>5</b>	<b>5.9</b>	<b>15</b>	<b>2</b>	<b>2</b>	<b>-2.7</b>	<b>1.2</b>	<b>225</b>
<b>BZX84C5V6LT1, G</b>	<b>Z3</b>	<b>5.2</b>	<b>5.6</b>	<b>6</b>	<b>40</b>	<b>4.8</b>	<b>6</b>	<b>400</b>	<b>5.2</b>	<b>6.3</b>	<b>10</b>	<b>1</b>	<b>2</b>	<b>-2.0</b>	<b>2.5</b>	<b>200</b>
<b>BZX84C6V2LT1, G</b>	<b>Z4</b>	<b>5.8</b>	<b>6.2</b>	<b>6.6</b>	<b>10</b>	<b>5.6</b>	<b>6.6</b>	<b>150</b>	<b>5.8</b>	<b>6.8</b>	<b>6</b>	<b>3</b>	<b>4</b>	<b>0.4</b>	<b>3.7</b>	<b>185</b>
BZX84C6V8LT1, G	Z5	6.4	6.8	7.2	15	6.3	7.2	80	6.4	7.4	6	2	4	1.2	4.5	155
BZX84C7V5LT1, G	Z6	7	7.5	7.9	15	6.9	7.9	80	7	8	6	1	5	2.5	5.3	140
BZX84C8V2LT1, G	Z7	7.7	8.2	8.7	15	7.6	8.7	80	7.7	8.8	6	0.7	5	3.2	6.2	135
BZX84C9V1LT1, G	Z8	8.5	9.1	9.6	15	8.4	9.6	100	8.5	9.7	8	0.5	6	3.8	7.0	130
BZX84C10LT1, G	Z9	9.4	10	10.6	20	9.3	10.6	150	9.4	10.7	10	0.2	7	4.5	8.0	130
BZX84C11LT1, G	Y1	10.4	11	11.6	20	10.2	11.6	150	10.4	11.8	10	0.1	8	5.4	9.0	130
<b>BZX84C12LT1, G</b>	<b>Y2</b>	<b>11.4</b>	<b>12</b>	<b>12.7</b>	<b>25</b>	<b>11.2</b>	<b>12.7</b>	<b>150</b>	<b>11.4</b>	<b>12.9</b>	<b>10</b>	<b>0.1</b>	<b>8</b>	<b>6.0</b>	<b>10.0</b>	<b>130</b>
BZX84C13LT1, G	Y3	12.4	13	14.1	30	12.3	14	170	12.5	14.2	15	0.1	8	7.0	11.0	120
BZX84C15LT1, G	Y4	13.8	15	15.6	30	13.7	15.5	200	13.9	15.7	20	0.05	10.5	9.2	13.0	110
BZX84C16LT1, G	Y5	15.3	16	17.1	40	15.2	17	200	15.4	17.2	20	0.05	11.2	10.4	14.0	105
<b>BZX84C18LT1, G</b>	<b>Y6</b>	<b>16.8</b>	<b>18</b>	<b>19.1</b>	<b>45</b>	<b>16.7</b>	<b>19</b>	<b>225</b>	<b>16.9</b>	<b>19.2</b>	<b>20</b>	<b>0.05</b>	<b>12.6</b>	<b>12.4</b>	<b>16.0</b>	<b>100</b>
BZX84C20LT1, G	Y7	18.8	20	21.2	55	18.7	21.1	225	18.9	21.4	20	0.05	14	14.4	18.0	85
BZX84C22LT1, G	Y8	20.8	22	23.3	55	20.7	23.2	250	20.9	23.4	25	0.05	15.4	16.4	20.0	85
BZX84C24LT1, G	Y9	22.8	24	25.6	70	22.7	25.5	250	22.9	25.7	25	0.05	16.8	18.4	22.0	80
Device	Device Marking	V <sub>Z1</sub> Below @ I <sub>ZT1</sub> = 2 mA			Z <sub>ZT1</sub> Below @ I <sub>ZT1</sub> = 2 mA	V <sub>Z2</sub> Below @ I <sub>ZT2</sub> = 0.1 mA		Z <sub>ZT2</sub> Below @ I <sub>ZT2</sub> = 0.5 mA	V <sub>Z3</sub> Below @ I <sub>ZT3</sub> = 10 mA		Z <sub>ZT3</sub> Below @ I <sub>ZT3</sub> = 10 mA	Max Reverse Leakage Current		θ <sub>VZ</sub> (mV/k) Below @ I <sub>ZT1</sub> = 2 mA		C (pF) @ V <sub>R</sub> = 0 f = 1 MHz
		Min	Nom	Max		Min	Max		Min	Max		I <sub>R</sub> (μA)	V <sub>R</sub> (V)	Min	Max	
BZX84C27LT1, G	Y10	25.1	27	28.9	80	25	28.9	300	25.2	29.3	45	0.05	18.9	21.4	25.3	70
BZX84C30LT1, G	Y11	28	30	32	80	27.8	32	300	28.1	32.4	50	0.05	21	24.4	29.4	70
BZX84C33LT1, G	Y12	31	33	35	80	30.8	35	325	31.1	35.4	55	0.05	23.1	27.4	33.4	70
BZX84C36LT1, G	Y13	34	36	38	90	33.8	38	350	34.1	38.4	60	0.05	25.2	30.4	37.4	70
BZX84C39LT1, G	Y14	37	39	41	130	36.7	41	350	37.1	41.5	70	0.05	27.3	33.4	41.2	45
BZX84C43LT1, G	Y15	40	43	46	150	39.7	46	375	40.1	46.5	80	0.05	30.1	37.6	46.6	40
BZX84C47LT1, G	Y16	44	47	50	170	43.7	50	375	44.1	50.5	90	0.05	32.9	42.0	51.8	40
BZX84C51LT1, G	Y17	48	51	54	180	47.6	54	400	48.1	54.6	100	0.05	35.7	46.6	57.2	40
BZX84C56LT1, G	Y18	52	56	60	200	51.5	60	425	52.1	60.8	110	0.05	39.2	52.2	63.8	40
BZX84C62LT1, G	Y19	58	62	66	215	57.4	66	450	58.2	67	120	0.05	43.4	58.8	71.6	35
BZX84C68LT1, G	Y20	64	68	72	240	63.4	72	475	64.2	73.2	130	0.05	47.6	65.6	79.8	35
BZX84C75LT1, G	Y21	70	75	79	255	69.4	79	500	70.3	80.2	140	0.05	52.5	73.4	88.6	35

3. Zener voltage is measured with a pulse test current  $I_Z$  at an ambient temperature of  $25^\circ\text{C}$ .

\* The "G" suffix indicates Pb-Free package available.

## BZX84B4V7LT1, BZX84C2V4LT1 Series

### ELECTRICAL CHARACTERISTICS – BZX84BxxxL (Tight Tolerance Series)

(Pinout: 1-Anode, 2-No Connection, 3-Cathode) ( $T_A = 25^\circ\text{C}$  unless otherwise noted,  $V_F = 0.90\text{ V Max.}$  @  $I_F = 10\text{ mA}$ )

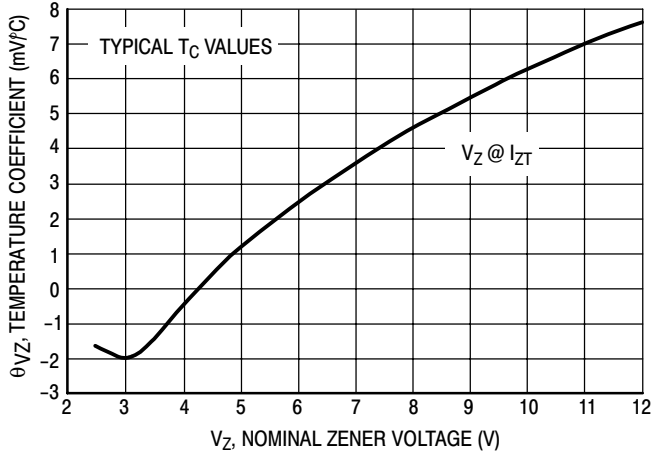
Device	Device Marking	$V_Z$ (Volts) @ $I_{ZT} = 5\text{ mA}$ (Note 4)			$Z_{ZT}$ ( $\Omega$ ) @ $I_{ZT} = 5\text{ mA}$ (Note 4)	Max Reverse Leakage Current		$\theta_{VZ}$ (mV/k) @ $I_{ZT} = 5\text{ mA}$		C (pF) @ $V_R = 0$ , f = 1 MHz
						Min	Nom			
		$\mu\text{A}$	@	Volts	Min			Max		
BZX84B4V7LT1, G	T10	4.61	4.7	4.79	80	3	2	-3.5	0.2	260
BZX84B5V1LT1, G	T11	5.00	5.1	5.20	60	2	2	-2.7	1.2	225
BZX84B5V6LT1, G	T12	5.49	5.6	5.71	40	1	2	-2	2.5	200
BZX84B6V2LT1, G	T13	6.08	6.2	6.32	10	3	4	0.4	3.7	185
BZX84B6V8LT1, G	T14	6.66	6.8	6.94	15	2	4	1.2	4.5	155
BZX84B7V5LT1, G	T15	7.35	7.5	7.65	15	1	5	2.5	5.3	140
BZX84B8V2LT1, G	T16	8.04	8.2	8.36	15	0.7	5	3.2	6.2	135
BZX84B9V1LT1, G	T17	8.92	9.1	9.28	15	0.5	6	3.8	7	130
BZX84B16LT1, G	T19	15.7	16	16.3	40	0.05	11.2	10.4	14	105
BZX84B18LT1, G	T20	17.6	18	18.4	45	0.05	12.6	12.4	16	100

4. Zener voltage is measured with a pulse test current  $I_Z$  at an ambient temperature of  $25^\circ\text{C}$ .

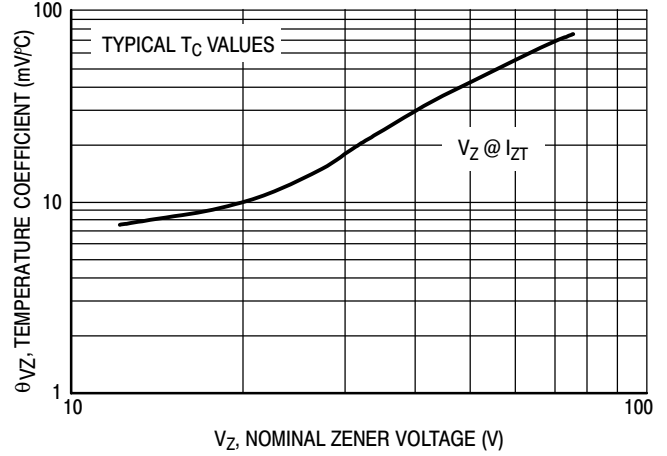
\* The "G" suffix indicates Pb-Free package available.

# BZX84B4V7LT1, BZX84C2V4LT1 Series

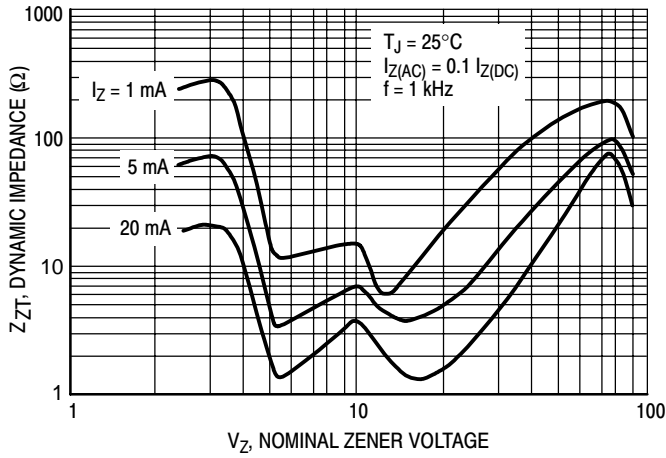
## TYPICAL CHARACTERISTICS



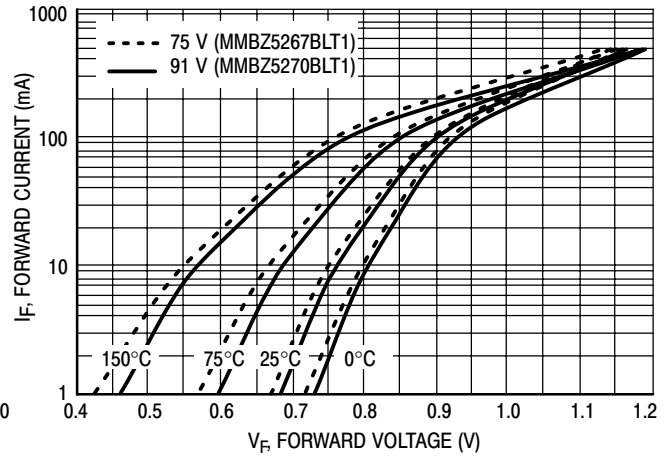
**Figure 1. Temperature Coefficients  
(Temperature Range -55°C to +150°C)**



**Figure 2. Temperature Coefficients  
(Temperature Range -55°C to +150°C)**



**Figure 3. Effect of Zener Voltage on  
Zener Impedance**



**Figure 4. Typical Forward Voltage**

# BZX84B4V7LT1, BZX84C2V4LT1 Series

## TYPICAL CHARACTERISTICS

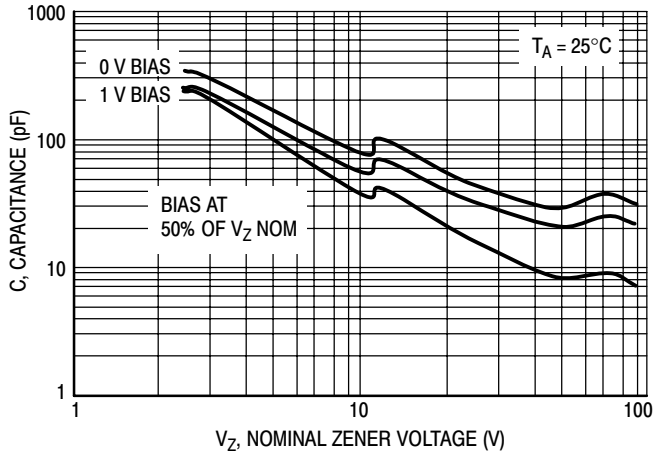


Figure 5. Typical Capacitance

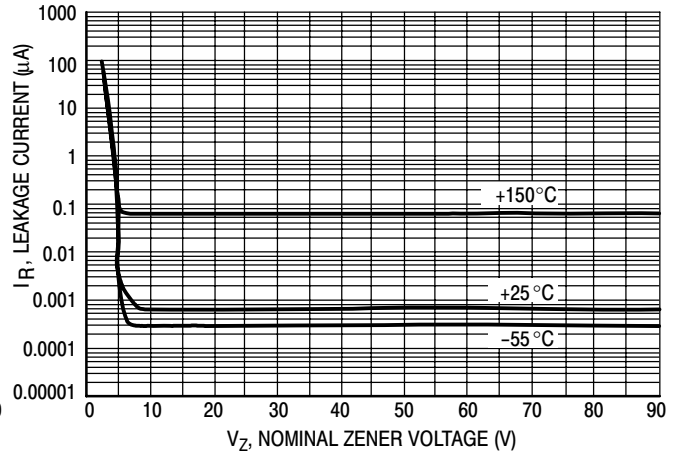


Figure 6. Typical Leakage Current

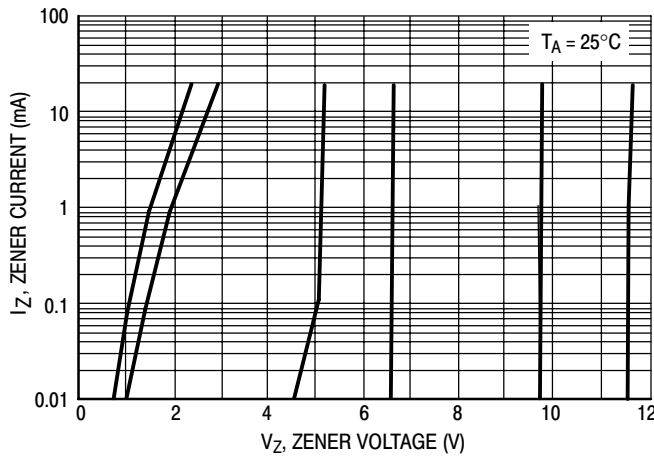


Figure 7. Zener Voltage versus Zener Current  
( $V_Z$  Up to 12 V)

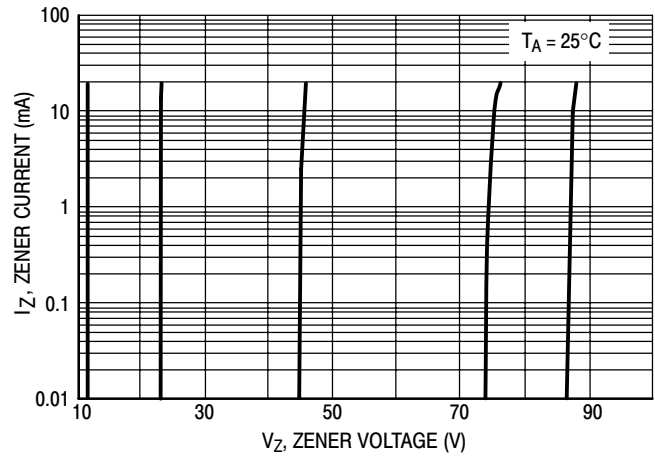
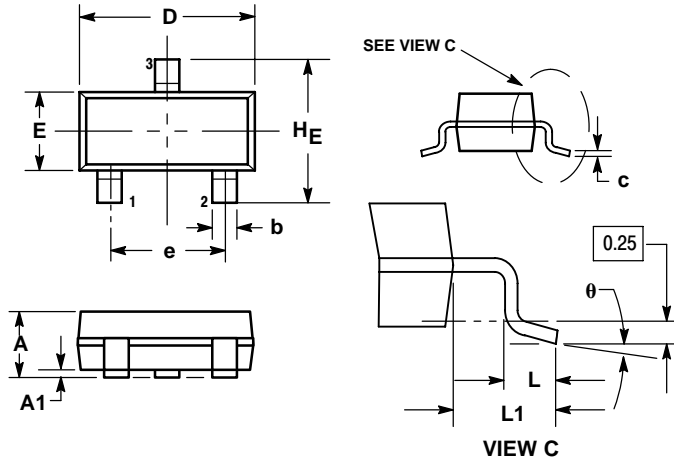


Figure 8. Zener Voltage versus Zener Current  
(12 V to 91 V)

# BZX84B4V7LT1, BZX84C2V4LT1 Series

## PACKAGE DIMENSIONS

SOT-23 (TO-236)  
CASE 318-08  
ISSUE AN

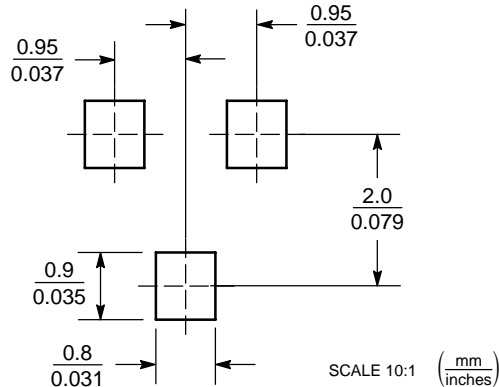


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
  4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

- STYLE 8:
1. ANODE
  2. NO CONNECTION
  3. CATHODE

## SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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